

TSD1858

Low Vcesat NPN Transistor



TO-251 (IPAK)



Pin Definition:

- 1. Base
- 2. Collector
- 3. Emitter

BV _{CBO}	180V
BV _{CEO}	160V
Ic	1.5A
V _{CE(SAT)}	0.3V @ I _C = 1A, I _B = 100mA

Features

- Low $V_{CE(SAT)}$ 0.15 @ $I_C = 1A$, $I_B = 100mA$ (Typ.)
- $High \; BV_{CEO}$

Structure

- **Epitaxial Planar Type**
- **NPN Silicon Transistor**

Ordering Information

PRODUCT SUMMARY

Part No.	Package	Packing
TSD1858CH C5G	TO-251	75pcs / Tube

Note: "G" denote for Halogen Free Product

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Collector-Base Voltage		V_{CBO}	180	V
Collector-Emitter Voltage		$V_{\sf CEO}$	160	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC		1.5	
	Pulse	Ic	3 (note1)	A
Power Dissipation @ T _A =25 °C		P_{D}	1	W
Power Dissipation @ T _C =25 °C		P_D	15	W
Thermal Resistance - Junction to Case		R⊖ _{JC}	125	°C/W
Thermal Resistance - Junction to Ambient		RΘ _{JA}	8.33	°C/W
Operating Junction Temperature		T _J	+150	°C
Operating Junction and Storage Temperature Range		T _{STG}	- 55 to +150	°C

Note: 1. Single pulse, Pw≤380us, Duty≤2%

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	BV _{CBO}	180		1	V
Collector-Emitter Breakdown Voltage	$I_{C} = 10 \text{mA}, I_{B} = 0$	BV _{CEO}	160		ŀ	V
Emitter-Base Breakdown Voltage	$I_E = 50uA, I_C = 0$	BV _{EBO}	5			V
Collector Cutoff Current	$V_{CB} = 160V, I_{E} = 0$	I _{CBO}			1	uA
Emitter Cutoff Current	$V_{EB} = 4V, I_{C} = 0$	I _{EBO}			1	uA
Collector-Emitter Saturation Voltage	I_{C} = 1A, I_{B} = 100mA	$V_{CE(SAT)}$		0.15	0.3	V
Base-Emitter Saturation Voltage	$V_{CE} = 5V, I_{C} = 5mA$	$V_{BE(ON)}$			0.8	V
DC Current Transfer Ratio	$V_{CE} = 5V, I_{C} = 200mA$	h _{FE} 1	180		390	
	$V_{CE} = 5V, I_{C} = 500mA$	h _{FE} 2	30			
Transition Frequency	V _{CE} =5V, I _E =150mA, f=100MHz	f _T		200		MHz
Output Capacitance	V _{CB} = 10V, f=1MHz	Cob		13		pF

Note: Pulse test: pulse width ≤380uS, Duty cycle≤2%

1/4 Version: E11







Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

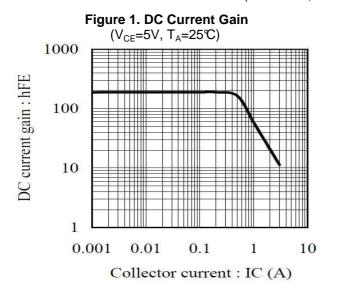


Figure 3. $V_{\text{BE(SAT)}}$ vs. Collector Current

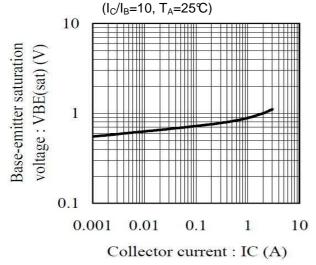


Figure 5. Frequency vs. Emitter Current

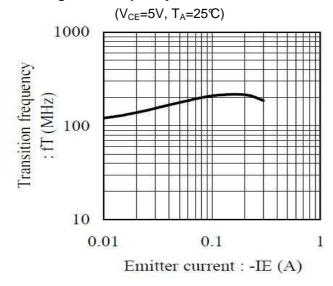


Figure 2. $V_{\text{CE(SAT)}}$ vs. Collector Current

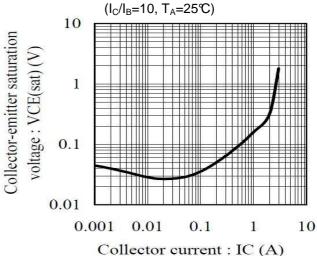


Figure 4. Cib vs. V_{CE}

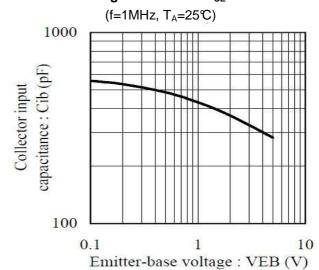
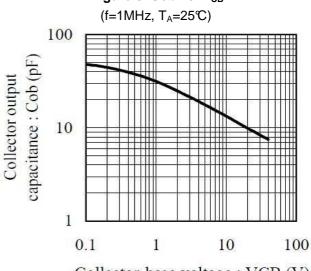


Figure 6. Cob vs. V_{CB}



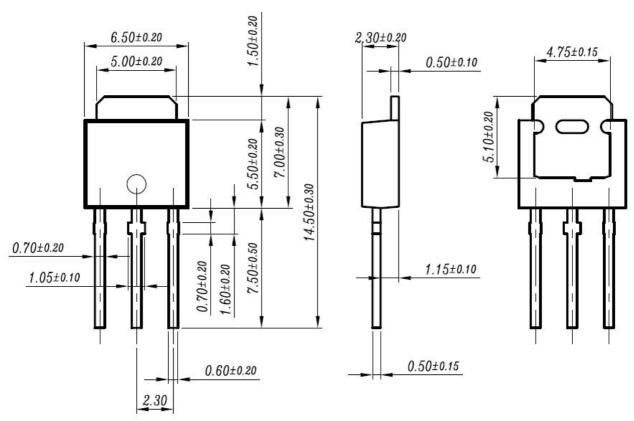
Collector-base voltage: VCB (V)

2/4 Version: E11



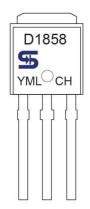


TO-251 Mechanical Drawing



Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code

3/4 Version: E11



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4/4 Version: E11